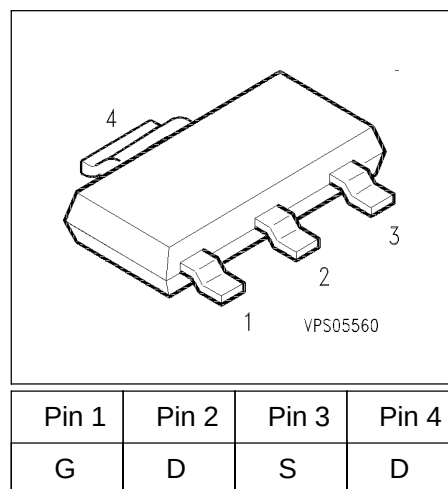


BSP 319

SIPMOS® Small-Signal Transistor

- N channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $V_{GS(th)} = 1.2 \dots 2.0 \text{ V}$



Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Marking
BSP 319	50 V	3.8 A	0.07Ω	SOT-223	BSP 319

Type	Ordering Code	Tape and Reel Information
BSP 319	Q67000-S273	E6327

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current $T_A = 29^\circ\text{C}$	I_D	3.8	A
DC drain current, pulsed $T_A = 25^\circ\text{C}$	I_{Dpuls}	15	
Avalanche energy, single pulse $I_D = 3.8 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \Omega$ $L = 6.2 \text{ mH}$, $T_j = 25^\circ\text{C}$	E_{AS}	90	mJ
Gate source voltage	V_{GS}	± 20	V
ESD Sensitivity (HBM) as per MIL-STD 883		Class 1	
Power dissipation $T_A = 25^\circ\text{C}$	P_{tot}	1.8	W

Maximum Ratings

Parameter	Symbol	Values	Unit
Chip or operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip to ambient air	R_{thJA}	≤ 70	K/W
Thermal resistance, junction-soldering point ¹⁾	R_{thJS}	≤ 10	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

1) Transistor on epoxy pcb 40 mm x 40 mm x 1,5 mm with 6 cm² copper area for drain connection

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Drain- source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = 0.25\text{ mA}$, $T_j = 0^\circ\text{C}$	$V_{(BR)DSS}$	50	-	-	V
Gate threshold voltage $V_{GS} = V_{DS}$, $I_D = 1\text{ mA}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25^\circ\text{C}$ $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125^\circ\text{C}$	I_{DSS}	- -	0.1 10	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	10	100	
Drain-Source on-state resistance $V_{GS} = 5\text{ V}$, $I_D = 2.4\text{ A}$	$R_{DS(on)}$	-	0.06	0.07	Ω

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Dynamic Characteristics

Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 2.4\text{ A}$	g_{fs}	3	8	-	S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	750	1000	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	240	360	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	120	180	
Turn-on delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_{GS} = 50\ \Omega$	$t_{d(on)}$	-	20	30	ns
Rise time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_{GS} = 50\ \Omega$	t_r	-	55	85	
Turn-off delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_{GS} = 50\ \Omega$	$t_{d(off)}$	-	210	260	
Fall time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_{GS} = 50\ \Omega$	t_f	-	120	160	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

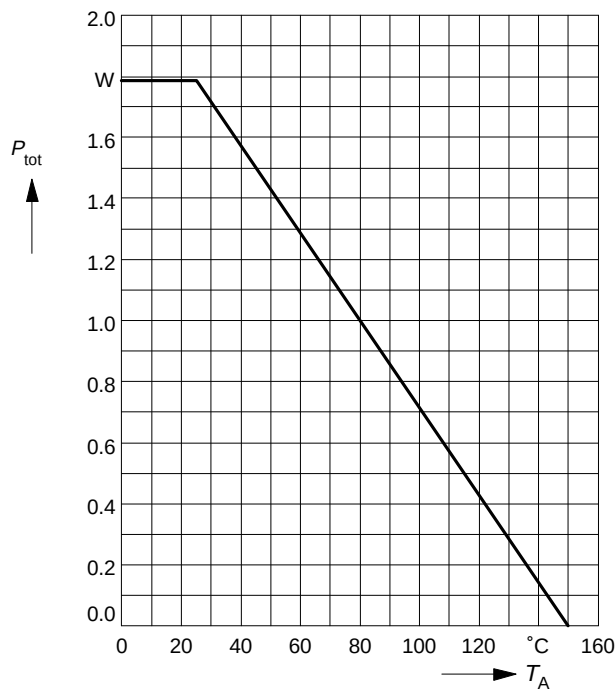
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Reverse Diode

Inverse diode continuous forward current $T_A = 25^\circ\text{C}$	I_S	-	-	3.8	A
Inverse diode direct current,pulsed $T_A = 25^\circ\text{C}$	I_{SM}	-	-	15	
Inverse diode forward voltage $V_{GS} = 0\text{ V}$, $I_F = 7.6\text{ A}$, $T_j = 25^\circ\text{C}$	V_{SD}	-	0.95	1.3	V
Reverse recovery time $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	50	-	ns
Reverse recovery charge $V_R = 30\text{ V}$, $I_F = I_S$, $di_F/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	0.07	-	μC

Power dissipation

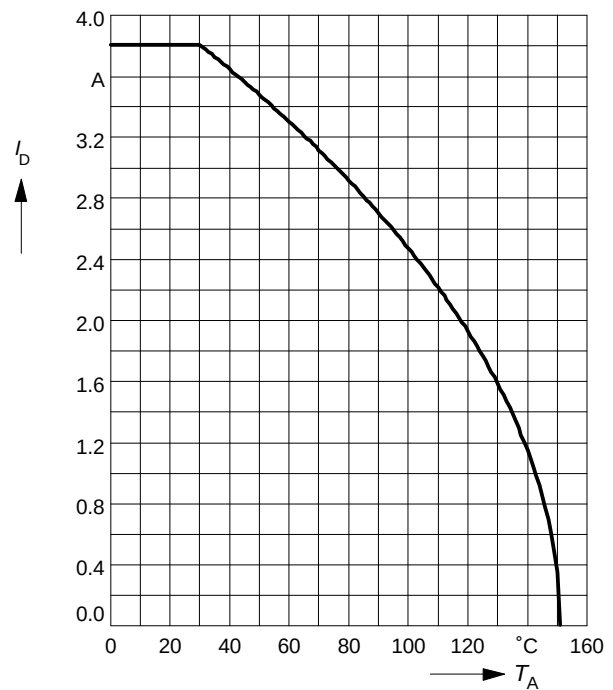
$$P_{\text{tot}} = f(T_A)$$



Drain current

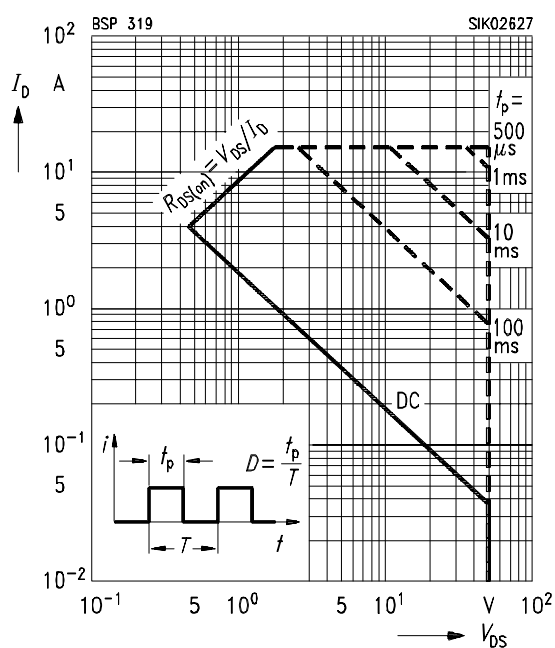
$$I_D = f(T_A)$$

parameter: $V_{GS} \geq 5 \text{ V}$



Safe operating area $I_D = f(V_{DS})$

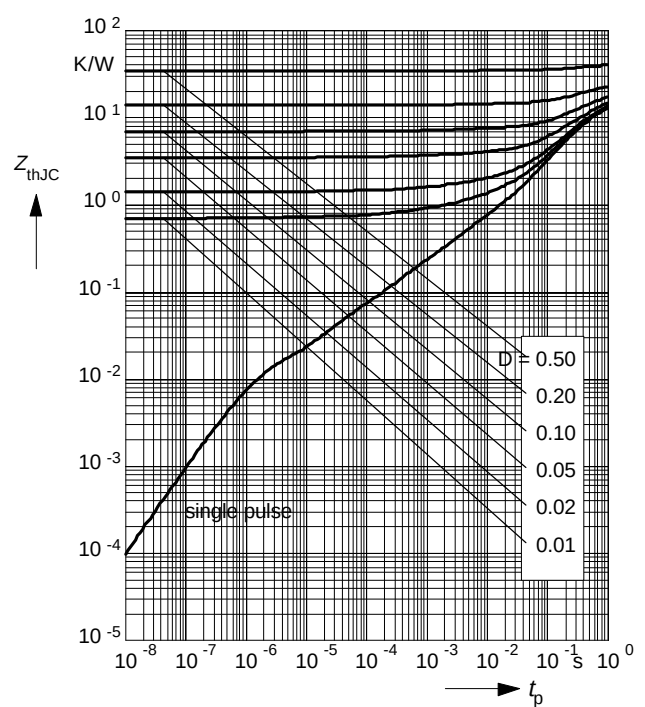
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



Transient thermal impedance

$$Z_{\text{th JA}} = f(t_p)$$

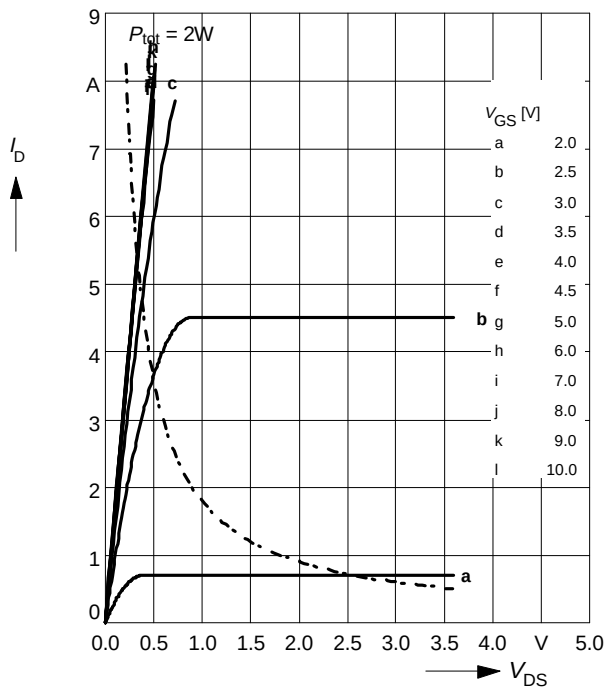
parameter: $D = t_p / T$



Typ. output characteristics

$$I_D = f(V_{DS})$$

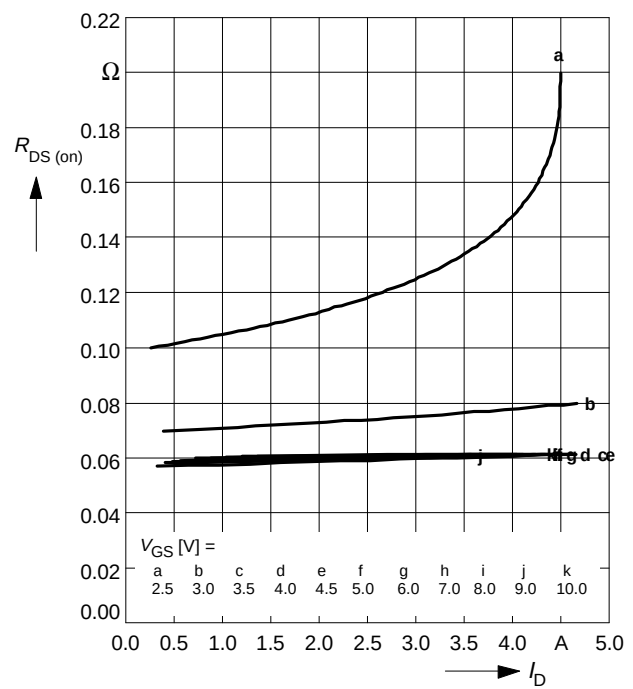
parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



Typ. drain-source on-resistance

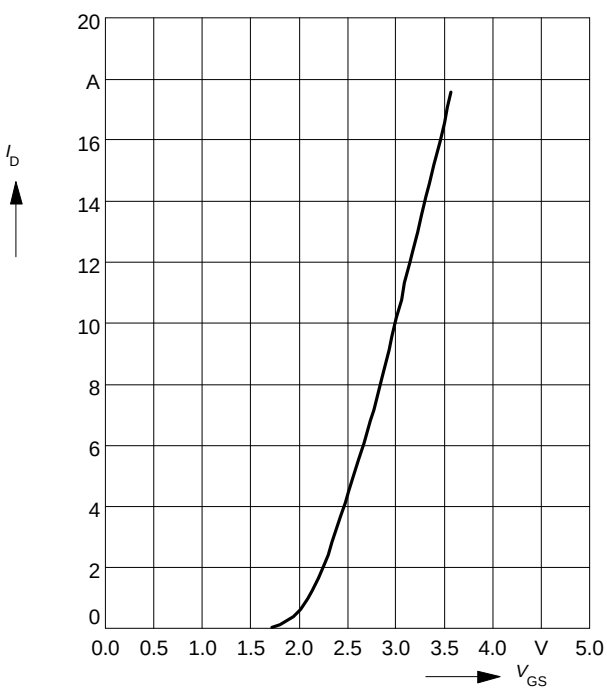
$$R_{DS(on)} = f(I_D)$$

parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



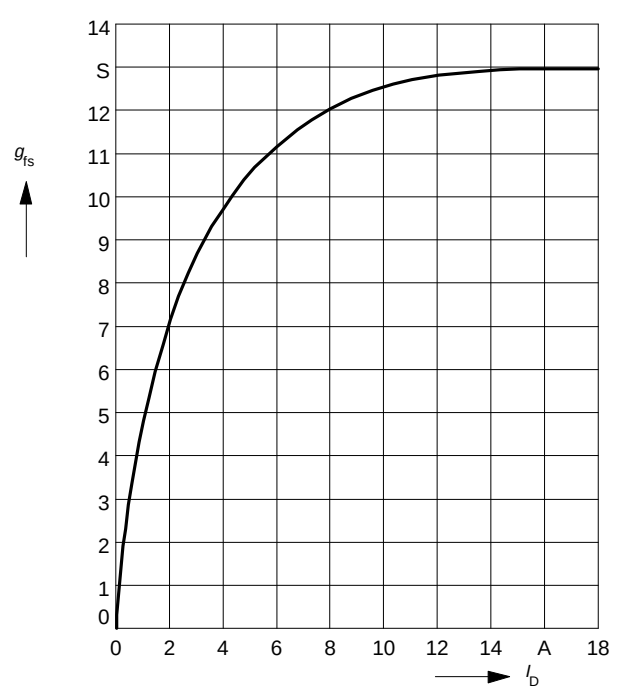
Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$



Typ. forward transconductance $g_{fs} = f(I_D)$

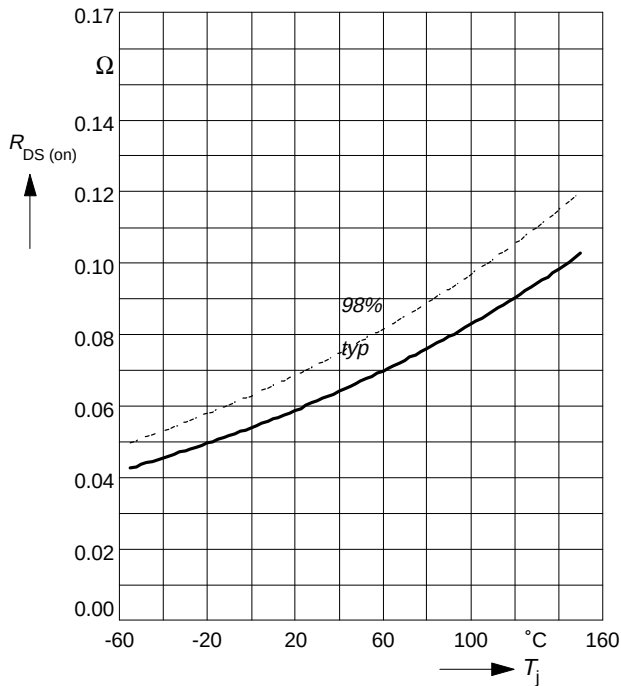
parameter: $t_p = 80 \mu s$,



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

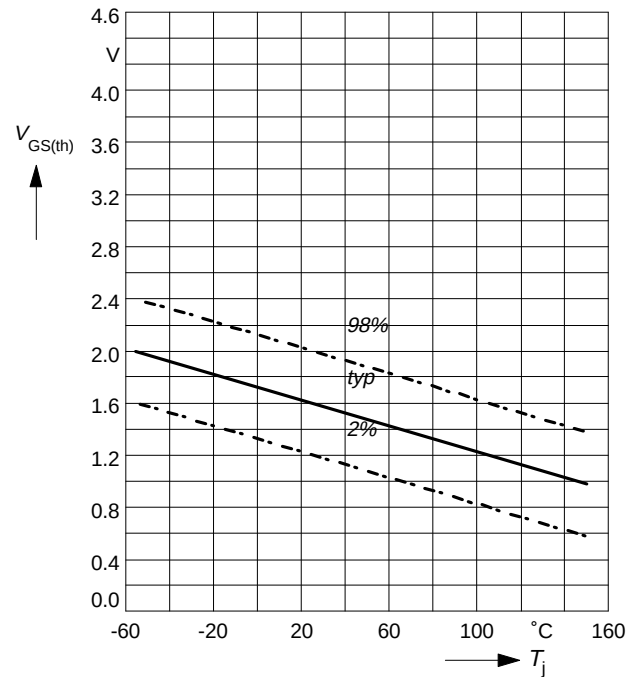
parameter: $I_D = 2.4 \text{ A}$, $V_{GS} = 5 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

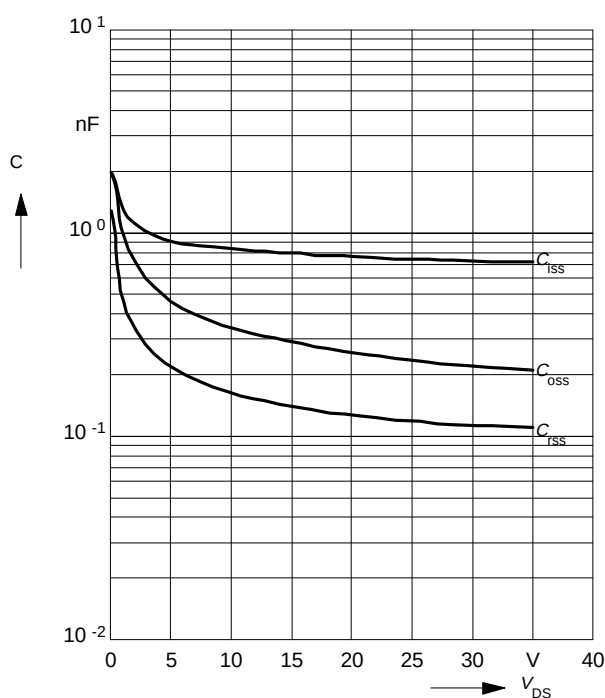
parameter: $V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$



Typ. capacitances

$$C = f(V_{DS})$$

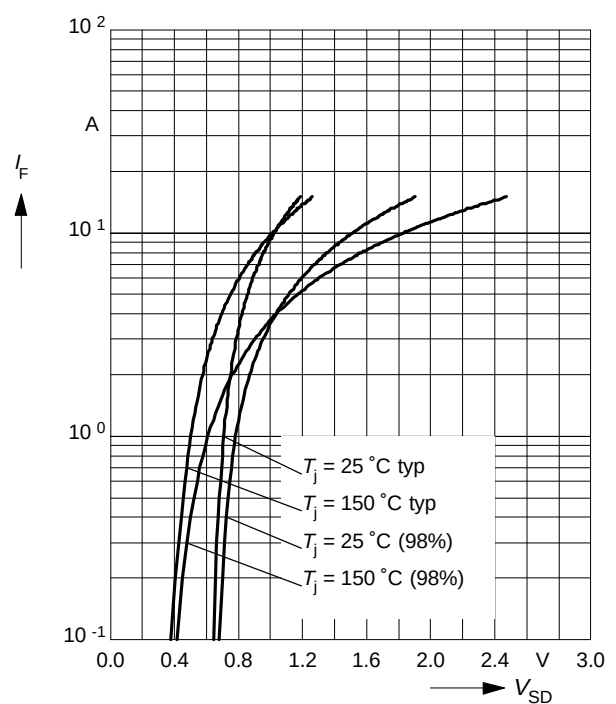
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



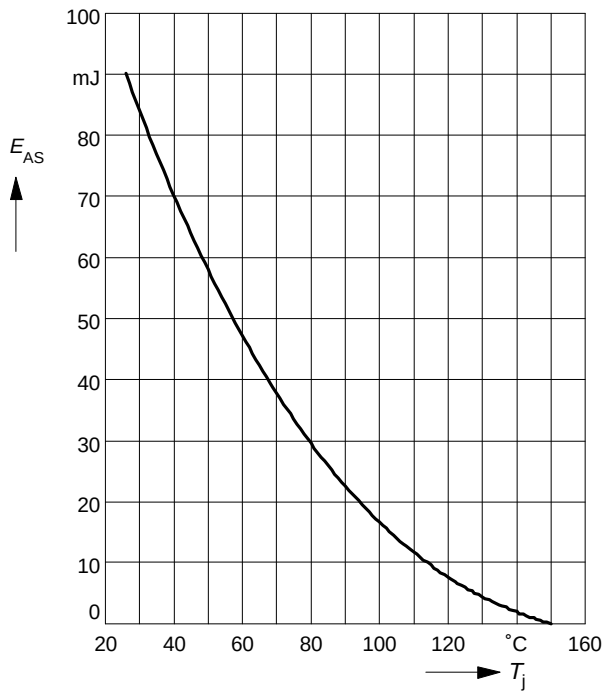
Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

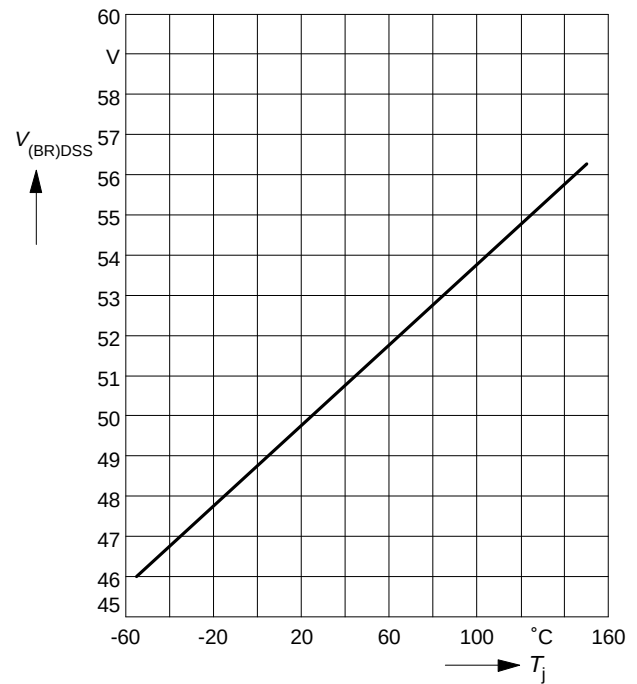
parameter: T_j , $t_p = 80 \mu\text{s}$



Avalanche energy $E_{AS} = f(T_j)$
 parameter: $I_D = 3.8 \text{ A}$, $V_{DD} = 25 \text{ V}$
 $R_{GS} = 25 \Omega$, $L = 6.2 \text{ mH}$



Drain-source breakdown voltage
 $V_{(BR)DSS} = f(T_j)$



Safe operating area $I_D = f(V_{DS})$
 parameter : $D = 0.01$, $T_C = 25^\circ\text{C}$

